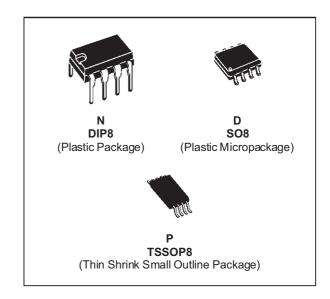


TL082 TL082A - TL082B

GENERAL PURPOSE J-FET DUAL OPERATIONAL AMPLIFIER

- WIDE COMMON-MODE (UP TO VCC⁺) AND DIFFERENTIAL VOLTAGE RANGE
- LOW INPUT BIAS AND OFFSET CURRENT
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J_FET INPUT STAGE
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE: 16V/µs (typ)



DESCRIPTION

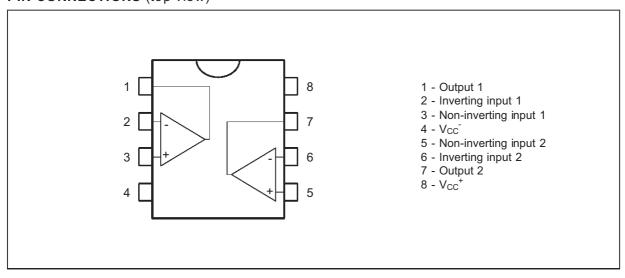
The TL082, TL082A and TL082B are high speed J–FET input dual operational amplifiers incorporating well matched, high voltage J–FET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset current, and low offset voltage temperature coefficient.

ORDER CODES

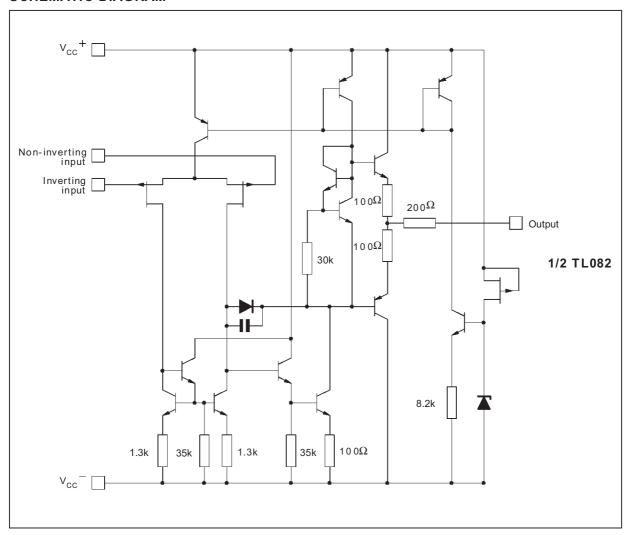
Part Number	Temperature	Package				
Fait Number	Range	N	D	Р		
TL082M/AM/BM	–55°C, +125°C	•	•	•		
TL082I/AI/BI	–40°C, +105°C	•	•	•		
TL082C/AC/BC	•	•	•			
Examples : TL082CD, TL082IN						

PIN CONNECTIONS (top view)



January 1999 1/10

SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
Vcc	Supply Voltage - (note 1)	±18	V	
Vi	Input Voltage - (note 3)	±15	V	
V _{id}	Differential Input Voltage - (note 2)	±30	V	
P _{tot}	Power Dissipation		680	mW
	Output Short-circuit Duration - (note 4)		Infinite	
T _{oper}		TL082C,AC,BC TL082I,AI,BI TL082M,AM,BM	0 to 70 -40 to 105 -55 to 125	°C
T _{stg}	Storage Temperature Range		-65 to 150	°C

- All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC}⁺ and V_{CC}⁻.
 Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
 The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
 The output may be shorted to ground or to either supply. Temperature and /or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

ELECTRICAL CHARACTERISTICS

 V_{CC} = ±15V, T_{amb} = 25 o C (unless otherwise specified)

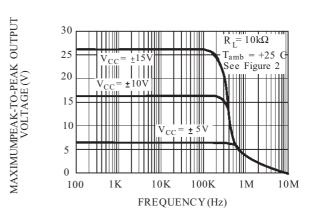
Symbol	Parameter		TL082I,M,AC,AI, AM,BC,BI,BM			TL082C		
		Min.	Тур.	Max.	Min.	Тур.	Max.	
V _{io}	$\begin{array}{c} \text{Input Offset Voltage } (R_S=50\Omega) \\ T_{amb}=25^{\circ}\text{C} & \text{TL082} \\ & \text{TL082A} \\ & \text{TL082B} \\ T_{min.} \leq T_{amb} \leq T_{max.} & \text{TL082} \\ & \text{TL082A} \\ & \text{TL082B} \\ \end{array}$		3 3 1	10 6 3 13 7 5		3	10	mV
DVio	Input Offset Voltage Drift		10			10		μV/°C
l _{io}	$\begin{array}{l} \text{Input Offset Current *} \\ T_{\text{amb}} = 25^{\circ}\text{C} \\ T_{\text{min.}} \leq T_{\text{amb}} \leq T_{\text{max.}} \end{array}$		5	100 4		5	100 4	pA nA
l _{ib}	Input Bias Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max.}$		20	200 20		20	400 20	pA nA
A _{vd}	Large Signal Voltage Gain ($R_L = 2k\Omega$, $V_O = \pm 10V$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		200		25 15	200		V/mV
SVR	Supply Voltage Rejection Ratio (R _S = 50Ω) $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max.}$		86		70 70	86		dB
Icc	Supply Current, per Amp, no Load $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		1.4	2.5 2.5		1.4	2.5 2.5	mA
V _{icm}	Input Common Mode Voltage Range		+15 -12		±11	+15 -12		V
CMR	Common Mode Rejection Ratio (R _S = 50Ω) $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max.}$	80 80	86		70 70	86		dB
los	Output Short-circuit Current $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max.}$	10 10	40	60 60	10 10	40	60 60	mA
±V _{OPP}	$ \begin{array}{ll} \text{Output Voltage Swing} \\ T_{amb} = 25^{^{O}}\text{C} & \text{R}_{L} = 2k\Omega \\ \text{R}_{L} = 10k\Omega \\ T_{min.} \leq T_{amb} \leq T_{max.} & \text{R}_{L} = 2k\Omega \\ \text{R}_{L} = 10k\Omega \\ \end{array} $	10 12 10 12	12 13.5		10 12 10 12	12 13.5		V
SR	Slew Rate (V_{in} = 10V, R_L = 2k Ω , C_L = 100pF, T_{amb} = 25°C, unity gain)	8	16		8	16		V/µs
t _r	Rise Time (V_{in} = 20mV, R_L = 2k Ω , C_L = 100pF, T_{amb} = 25°C, unity gain)		0.1			0.1		μs
Kov	Overshoot (V_{in} = 20mV, R_L = 2k Ω , C_L = 100pF, T_{amb} = 25°C, unity gain)		10			10		%
GBP	Gain Bandwidth Product (f = 100kHz, T_{amb} = 25°C, V_{in} = 10mV, R_L = 2k Ω , C_L = 100pF)	2.5	4		2.5	4		MHz
Ri	Input Resistance		10 ¹²			10 ¹²		Ω
THD	Total Harmonic Distortion (f = 1kHz, A_V = 20dB, R_L = 2k Ω , C_L = 100pF, T_{amb} = 25°C, V_O = 2 V_{PP})		0.01			0.01		%
en	Equivalent Input Noise Voltage (f = 1kHz, $R_s = 100\Omega$)		15			15		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$
Øm	Phase Margin		45			45		Degree
V ₀₁ /V ₀₂	Channel Separation (A _v = 100)		120			120		dB

^{*} The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature.

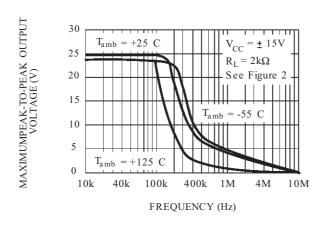
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY

V_{CC} = ± 15V $R_L = 2k\Omega$ MAXIMUM PEAK-TO-PEAKOUTPUT 25 See Figure 2 20 VOLTAGE (V) ± 10V 15 10 = ± 5V 5 100K 1K 10K 1M 10M 100 FREQUENCY (Hz)

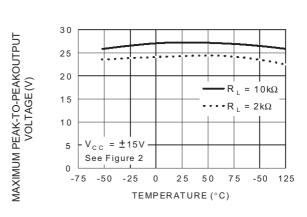
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



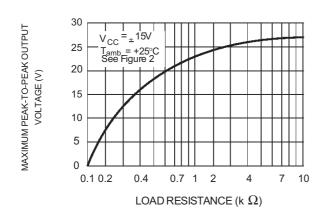
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



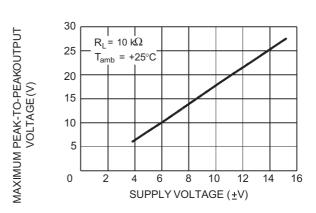
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREE AIR TEMP.



MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS LOAD RESISTANCE

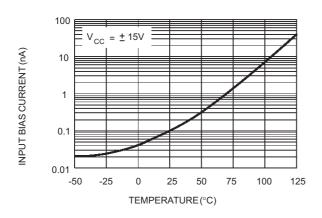


MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS SUPPLY VOLTAGE

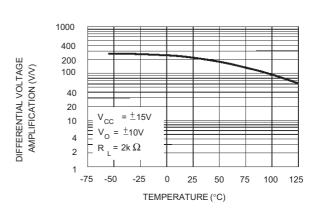


47/

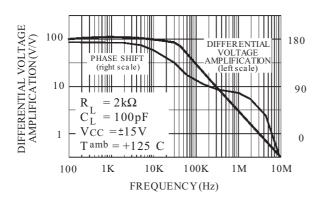
INPUT BIAS CURRENT VERSUS FREE AIR TEMPERATURE



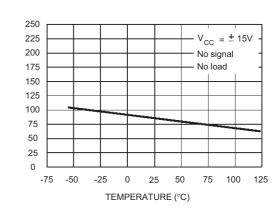
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION VERSUS FREE AIR TEMPERATURE



LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT VERSUS FREQUENCY

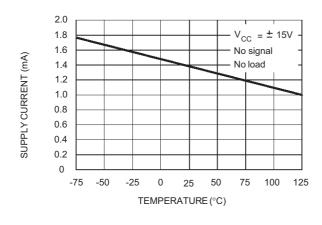


TOTAL POWER DISSIPATION VERSUS FREE AIR TEMPERATURE

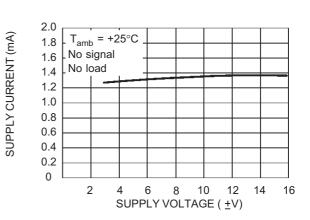


TOTAL POWER DISSIPATION (mW)

SUPPLY CURRENT PER AMPLIFIER VERSUS FREE AIR TEMPERATURE

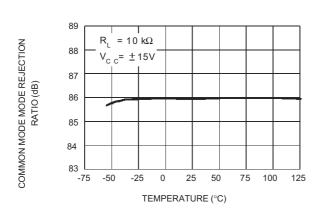


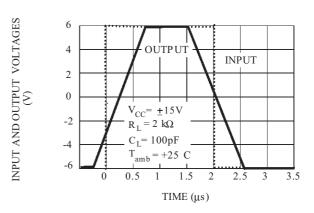
SUPPLY CURRENT PER AMPLIFIER VERSUS SUPPLY VOLTAGE



COMMON MODE REJECTION RATIO VERSUS FREE AIR TEMPERATURE

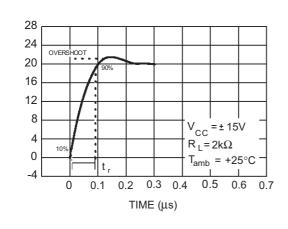
VOLTAGE FOLLOWER LARGE SIGNAL PULSE RESPONSE



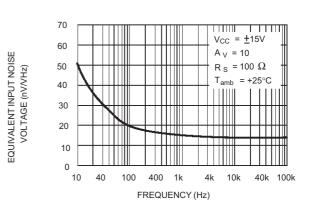


OUTPUT VOLTAGE VERSUS ELAPSED TIME

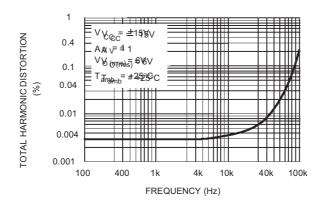
EQUIVALENT INPUT NOISE VOLTAGE VERSUS FREQUENCY



OUTPUT VOLTAGE (mV)



TOTAL HARMONIC DISTORTION VERSUS FREQUENCY



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PARAMETER MEASUREMENT INFORMATION

Figure 1: Voltage Follower

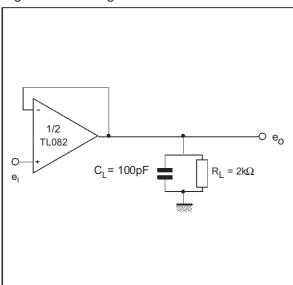
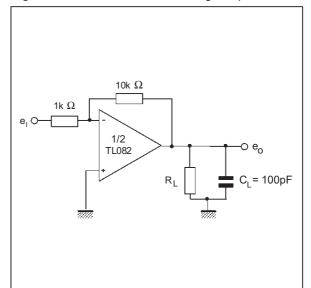
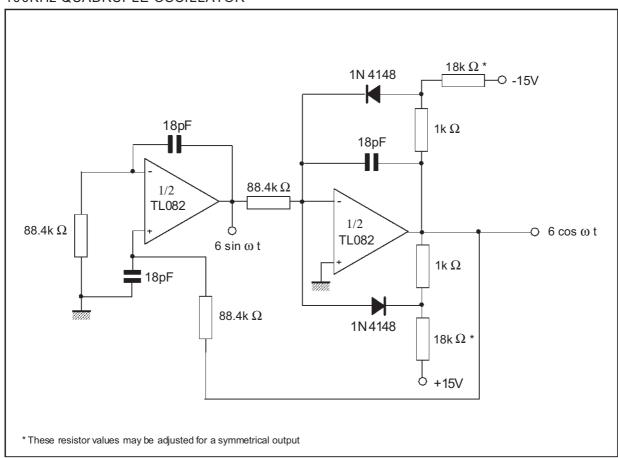


Figure 2: Gain-of-10 Inverting Amplifier



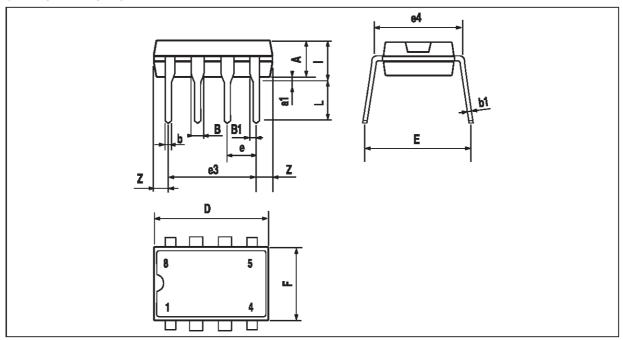
TYPICAL APPLICATION

100KHz QUADRUPLE OSCILLATOR



PACKAGE MECHANICAL DATA

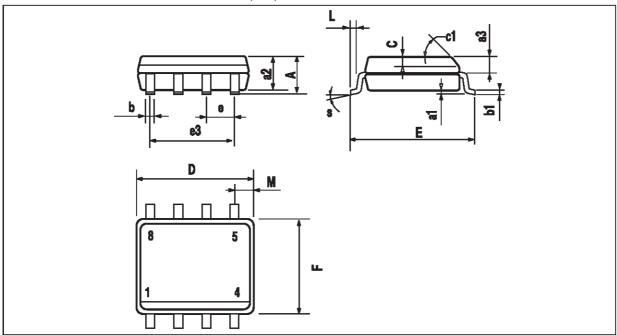
8 PINS - PLASTIC DIP



Dimensions	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А		3.32			0.131		
a1	0.51			0.020			
В	1.15		1.65	0.045		0.065	
b	0.356		0.55	0.014		0.022	
b1	0.204		0.304	0.008		0.012	
D			10.92			0.430	
Е	7.95		9.75	0.313		0.384	
е		2.54			0.100		
e3		7.62			0.300		
e4		7.62			0.300		
F			6.6			0260	
i			5.08			0.200	
L	3.18		3.81	0.125		0.150	
Z			1.52			0.060	

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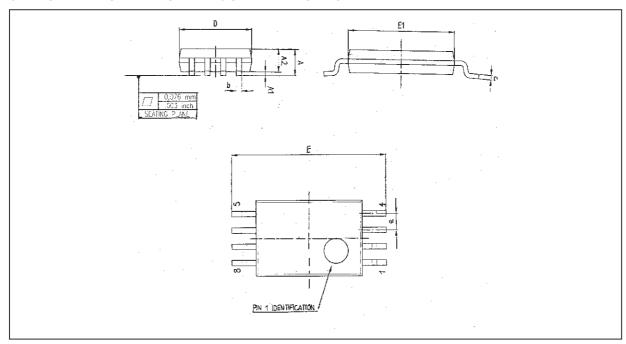
PACKAGE MECHANICAL DATA 8 PINS - PLASTIC MICROPACKAGE (SO)



Dimensions	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.75			0.069	
a1	0.1		0.25	0.004		0.010	
a2			1.65			0.065	
а3	0.65		0.85	0.026		0.033	
b	0.35		0.48	0.014		0.019	
b1	0.19		0.25	0.007		0.010	
С	0.25		0.5	0.010		0.020	
c1			45°	(typ.)			
D	4.8		5.0	0.189		0.197	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		3.81			0.150		
F	3.8		4.0	0.150		0.157	
L	0.4		1.27	0.016		0.050	
М			0.6			0.024	
S	8° (max.)						

PACKAGE MECHANICAL DATA

8 PINS - THIN SHRINK SMALL OUTLINE PACKAGE



Dim.	Millimeters			Inches			
Dilli.	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α			1.20			0.05	
A1	0.05		0.15	0.01		0.006	
A2	0.80	1.00	1.05	0.031	0.039	0.041	
b	0.19		0.30	0.007		0.15	
С	0.09		0.20	0.003		0.012	
D	2.90	3.00	3.10	0.114	0.118	0.122	
Е		6.40			0.252		
E1	4.30	4.40	4.50	0.169	0.173	0.177	
е		0.65			0.025		
k	0°		8°	0°		8°	
1	0.50	0.60	0.75	0.09	0.0236	0.030	

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